

What is claimed is:

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1. A method of forming a liquid crystal display panel, comprising the steps of:

forming a common electrode on a first substrate;

forming a plurality of conductive contact dots on a second substrate;

forming a seal pattern on the second substrate, the seal pattern having a plurality of triangular bent portions that each have a vertex that is directed toward an inside of the second substrate, wherein each triangular bent portion circumvents a conductive contact dot;

assembling the first substrate and the second substrate; and

forming a liquid crystal layer between the first and second substrates.

N/E
2. The method according to claim 1, wherein the conductive contact dot comprises a silver (Ag).

A2
3. The method according to claim 1, wherein the triangular bent portions each include a first vertex, a second vertex, and a third vertex.

4. The method according to claim 3, wherein the first vertex, the second vertex, and the third vertex all have a rounded shape that is defined by a radius.

5. The method according to claim 4, wherein the radius is 0.5 to 2 millimeters.

A2
Concl'd

6. The method according to claim 4, wherein a distance between a first vertex and a second vertex is 5 to 20 millimeters.

7. The method according to claim 4, wherein a distance between a conductive contact dot and a third vertex is 0.1 to 5 millimeters.

8. The method according to claim 1, wherein the seal pattern is formed by a dispenser.

9. A method of forming a liquid crystal display panel, comprising the steps of:

forming a common electrode on a first substrate;

forming a plurality of conductive contact dots on the second substrate;

forming a seal pattern on the second substrate, the seal pattern having a plurality of semicircular bent portions, the semicircular bent portions being bent toward an inside of the second substrate wherein each semicircular bent portion circumvents a conductive contact dot;

assembling the first substrate and the second substrate; and

forming a liquid crystal layer between first and second substrates.

N/E

10. The method according to claim 9, wherein each of the two ends of the semicircular portion has a radius of 0.5 to 2 mm.

A3 11. The method according to claim 9, wherein the semicircular portion has

a radius of 2.5 to 10 millimeters.

12. The method according to claim 9, wherein a distance between a

conductive contact dot and a semicircular portion is 0.1 to 5 millimeters.